

# ABSTRACT OF THE DISCLOSURE

A method of fabricating a memory capable of improving the strength of a signal read from a memory cell is provided. This method of fabricating a memory comprises

5 steps of forming a storage part and an etched thin-film part by partially etching a storage material film formed on a first electrode film by a prescribed thickness, forming an insulator film to cover at least the thin-film part of the storage material film and patterning the

10 insulator film and the thin-film part of the storage material film by forming an etching mask on a prescribed region of the insulator film and thereafter etching the insulator film and the thin-film part of the storage material film through the etching mask.